

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4	((("6653698") or ("6352913")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/17 10:51
S2	0	S1 and "CMOS" and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/17 10:53
S3	10	"CMOS" and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal and nitrogen and aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:32
S4	1	"CMOS" and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal and nitrogen and aluminum and "sulfuric acid" and "hydrogen peroxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 10:55
S5	1	n-mos and p-mos and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal and nitrogen and aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 10:55
S6	2243	n-mos and p-mos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:33
S7	176	n-mos and p-mos and n-well and p-well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:33

## EAST Search History

S8	6	n-mos and p-mos and n-well and p-well and ("gate dielectric" near4(semiconductor or wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:34
S9	4	n-mos and p-mos and n-well and p-well and ("gate dielectric" near4(semiconductor or wafer or substrate)) and buffer and etch and metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:34
S10	3	n-mos and p-mos and n-well and p-well and ("gate dielectric" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:35
S11	0	n-mos and p-mos and n-well and p-well and ("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:35
S12	2	n-mos and p-mos and n-well and p-well and ("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:36
S13	156	("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 11:36
S14	29	("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal and p-well and n-well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:22
S15	25	"CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:23

## EAST Search History

S16	1	"CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" and "hydrofluoric acid" and anneal and temperature and ("PVD" or "CVD" or "ALD") and (titanium or hafnium or tantalum) and alloy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:25
S17	4	"CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" and "hydrofluoric acid" and anneal and temperature and ("PVD" or "CVD" or "ALD") and (titanium or hafnium or tantalum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:53
S18	1	"CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" and "hydrofluoric acid" and anneal and temperature and ("PVD" or "CVD" or "ALD") and (titanium or hafnium or tantalum) and electronegativ\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:25
S19	921	hafnium and tantalum and titanium and "CMOS"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:53
S20	11	hafnium and tantalum and titanium and "CMOS" and "aluminum nitride" and electronegativ\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:54
S21	1	hafnium and tantalum and titanium and "CMOS" and "aluminum nitride" and electronegativ\$4 and n-mos and p-mos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:54
S22	9	hafnium and tantalum and titanium and "CMOS" and "aluminum nitride" and electronegativ\$4 and energy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:57
S23	188	hafnium and "CMOS" and "aluminum nitride" and electronegativ\$4 and energy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:57

## EAST Search History

S24	9	hafnium and tantalum and "CMOS" and "aluminum nitride" and electronegativ\$4 and energy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:58
S25	2180	"CMOS" and "metal gate"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 12:59
S26	4	"CMOS" and "metal gate" and "aluminum nitride" and electronegativity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:04
S27	234	"aluminum nitride" and electronegativity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:07
S28	2	("aluminum nitride" near4 electronegativity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:06
S29	0	("aluminum nitride" near4 electronegativity) and hafnium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:06
S30	192	"aluminum nitride" and electronegativity and hafnium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:07
S31	13	"aluminum nitride" and electronegativity and hafnium and tantalum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:11

## EAST Search History

S32	10	"metal gate" and (dielectric or oxide) and electronegativity and hafnium and tantalum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:11
S33	2	"metal gate" and (dielectric or oxide) and electronegativity and hafnium and tantalum and "aluminum nitride"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/17 13:11